

Appl. No. 10/751,184
Amendment dated
Reply to OA of May 2, 2005

Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1. (Currently amended) A method for etching a metal layer having an oxide-based antireflective coating (ARC) layer thereon, comprising the steps of:

~~dry cleaning the ARC layer~~ performing a first dry cleaning process in an etching chamber with an oxide-based gas; and

~~etching at least part of the metal layer~~ performing a second dry cleaning process in the chamber with a gas mixture comprising Cl_2 and CHF_3 ,

wherein the first and second dry cleaning processes are carried out before etching the metal layer to eliminate byproducts remained in the chamber.

2.(Previously presented) The method of claim 1, wherein a flow rate of the Cl_2 ranges from about 100 sccm to about 200 sccm.

3.(Previously presented) The method of claim 1, wherein a flow rate of the CHF_3 ranges from about 5 sccm to about 30 sccm.

4.(Currently amended) The method of claim 1, wherein a pressure of each of the ~~cleaning and etching steps~~ the dry cleaning processes ranges from about 8m Torr to about 50m Torr.

Appl. No. 10/751,184
Amendment dated
Reply to OA of May 2, 2005

5.(Currently amended) The method of claim 1, wherein a source power of each of ~~the dry cleaning and etching steps~~ the dry cleaning processes ranges from about 500 W to about 1200 W.

6.(Currently amended) The method of claim 1, wherein a bias power of each of ~~the dry cleaning and etching steps~~ the dry cleaning processes ranges from about 0 W to about 10 W.

7.(Currently amended) The method of claim 1, wherein the dry cleaning process ~~method~~ processes are performed for about 5 seconds to about 30 seconds.

8.(Previously presented) The method of claim 1, wherein the oxide-based gas comprises oxygen.

9.(Currently amended) The method of claim 1, wherein the dry cleaning and etching steps processes are performed sequentially in a single etching chamber.

10.(Currently amended) The method of claim 1, wherein the metal layer and the ARC layer are on a wafer having a center area and an edge area, and the etching step dry cleaning processes decreases a microloading effect in the edge area upon etching the metal layer.

11.(Previously presented) The method of claim ~~44~~10, wherein the metal layer is etched at a rate that is substantially the same in the center area and the edge area.

Appl. No. 10/751,184
Amendment dated
Reply to OA of May 2, 2005

12.(Cancelled)

13.(Currently amended) The method of claim 1, wherein ~~the etching step further eliminates aluminum and silicon containing byproducts~~ the byproducts remained in the chamber comprise aluminum and silicon-containing polymers.

14.(Previously presented) The method of claim 1, wherein the metal layer comprises an aluminum layer.

15.(Previously presented) The method of claim 14, wherein the metal layer further comprises a titanium nitride layer under the aluminum layer.

16.(Previously presented) The method of claim 1, wherein the ARC layer comprises a silicon oxide.

RECEIVED
CENTRAL FAX CENTER

AUG 05 2005

Docket No. PLA31069/ANS/US

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF:

Sang Hun Oh

: GROUP ART UNIT:

SERIAL NO: 10/751,184

:

FILED: December 30, 2003

: EXAMINER:

FOR: Method for Etching a Metal Layer in a Semiconductor Device

I hereby certify that this document is being deposited with the United States Postal Service as first class mail in an envelope addressed to Commissioner for Patents, Washington, D.C. 20231, on January 27, 2004.

By:

Andrew D. Fortney, Ph.D.CLAIM FOR PRIORITY UNDER 35 U.S.C. 119(a)-(b) AND 37 C.F.R. 1.55COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Applicant respectfully requests under the Paris Convention for the Protection of Intellectual Property the benefit of the filing date of the prior foreign application(s) identified below:

<u>Serial No.</u>	<u>Filing Date</u>	<u>Country of Filing</u>
10-2002-0086802	December 30, 2002	Republic of KOREA

A certified copy of the above-identified priority application is attached.

Respectfully submitted,

Andrew D. Fortney, Ph.D.
Reg. No. 34,6007257 N. Maple Avenue, Bldg. D, #107
Fresno, California 93720
(559) 299 - 0128



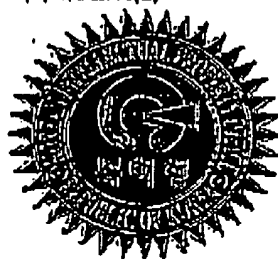
별첨 사본은 아래 출원의 원본과 동일함을 증명함.

This is to certify that the following application annexed hereto
is a true copy from the records of the Korean Intellectual
Property Office.

출원 번호 : 10-2002-0086802
Application Number

출원 년 월 일 : 2002년 12월 30일
Date of Application DEC 30, 2002

출원인 : 아남반도체 주식회사
Applicant(s) ANAM SEMICONDUCTOR., Ltd.



2003 년 10 월 10 일

특 허 청

COMMISSIONER

